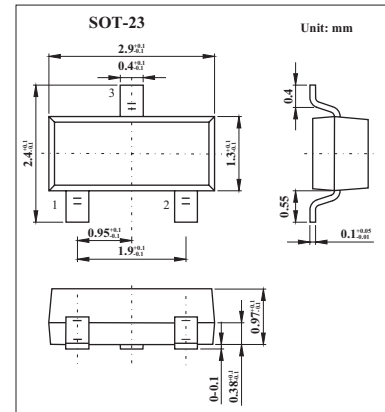


Schottky barrier (double) diodes

BAT754 series



■ Features

- Ultra high switching speed
- Guard ring protected
- Small plastic SMD package
- Low diode capacitance.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			30	V
Continuous forward current	I_F			200	mA
Repetitive peak forward current	I_{FRM}	$t_p < 1 \text{ s}; \delta < 0.5$		300	mA
Non-repetitive peak forward current	I_{FSM}	$t_p = 8.3 \text{ ms}$ half sinewave; JEDEC method		600	mA
Storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
Junction temperature	T_j			125	$^\circ\text{C}$
Operating ambient temperature	T_{amb}		-65	+125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Forward voltage	V_F	$I_F = 0.1 \text{ mA}$		200	mV
		$I_F = 1 \text{ mA}$		260	mV
		$I_F = 10 \text{ mA}$		340	mV
		$I_F = 30 \text{ mA}$		420	mV
		$I_F = 100 \text{ mA}$	600		mV
Reverse current	I_R	$V_R = 25 \text{ V}$; Note 1		2	μA
Diode capacitance	C_d	$f = 1 \text{ MHz}$; $V_R = 1 \text{ V}$		10	pF

Note

1. Pulse test: $t_p < 300 \mu\text{s}$; $\delta \leq 0.02$.

■ Marking

Type	BAT754	BAT754A	BAT754C	BAT754S
Marking	2K	2L	2M	2N